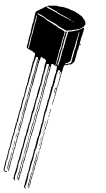
2N5221 (SILICON)

PNP SILICON ANNULAR TRANSISTOR

. . . designed for low-power, large signal audio and general-purpose amplifier applications. Complements NPN type 2N5220.

- Low Saturation Voltage – $V_{CE(sat)}$ = 0.5 Vdc (Max) @ I_C = 150 mAdc, I_B = 15 mAdc

PNP SILICON AMPLIFIER TRANSISTOR



*MAXIMUM RATINGS

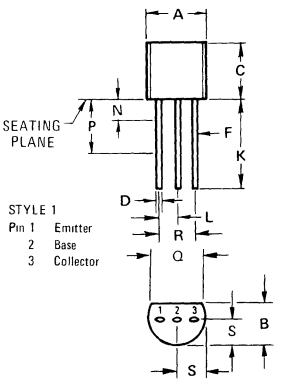
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CB}	15	Vdc
Emitter-Base Voltage	V_{EB}	3.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	310 350 2.8 2.73	mW mW/°C
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J,T_{stg}	-55 to +135 -55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Ambient	$R_{\theta JA}$(1)	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

*Indicates JEDEC Registered Data.

(1) $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.450	5.200	0.175	0.205
B	3.180	4.190	0.125	0.165
C	4.320	5.330	0.170	0.210
D	0.407	0.533	0.016	0.021
F	0.407	0.482	0.016	0.019
K	12.700	–	0.500	–
L	1.150	1.390	0.045	0.055
N	–	1.270	–	0.050
P	6.350	–	0.250	–
Q	3.430	–	0.135	–
R	2.410	2.670	0.095	0.105
S	2.030	2.670	0.080	0.105

CASE 29-02
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*ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (1) (I_C = 10 mAdc, I_B = 0)	BV_{CEO}	15	–	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	BV_{CBO}	15	–	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	BV_{EBO}	3.0	–	Vdc
Collector Cutoff Current (V_{CB} = 10 Vdc, I_E = 0)	I_{CBO}	–	100	nAdc
Emitter Cutoff Current (V_{BE} = 3.0 Vdc, I_C = 0)	I_{EBO}	–	100	nAdc
ON CHARACTERISTICS (1)				
DC Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 50 mAdc, V_{CE} = 10 Vdc)	h_{FE}	25 30	– 600	–
Collector-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{CE(sat)}$	–	0.5	Vdc
Base-Emitter Saturation Voltage (I_C = 150 mAdc, I_B = 15 mAdc)	$V_{BE(sat)}$	–	1.1	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain – Bandwidth Product (I_C = 20 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	f_T	100	–	MHz
Collector-Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	–	15	pF
Small-Signal Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	30	1800	–

*Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.